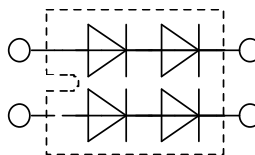


HiPerDynFRED

High Performance Dynamic Fast Recovery Diode
Extreme Low Loss and Soft Recovery
Parallel legs with series connected dice

Part number

DSEP2x25-12C



Backside: isolated

E72873

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package:

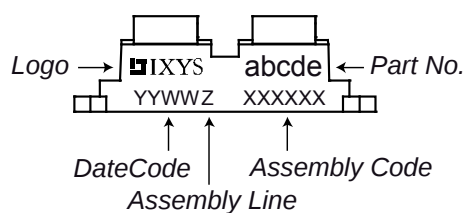
- Housing: SOT-227B (minibloc)
- Industry standard outline
- Cu base plate internal DCB isolated
- Isolation Voltage 3000 V
- Epoxy meets UL 94V-0
- RoHS compliant

Ratings

Symbol	Definition	Conditions			min.	typ.	max.	Unit
V _{RRM}	max. repetitive reverse voltage			T _{VJ} = 25 °C			1200	V
I _R	reverse current	V _R = 1200 V		T _{VJ} = 25 °C			250	μA
		V _R = 1200 V		T _{VJ} = 150 °C			2	mA
V _F	forward voltage	I _F = 25 A		T _{VJ} = 25 °C			4.71	V
		I _F = 50 A					5.92	V
		I _F = 25 A		T _{VJ} = 150 °C			2.95	V
		I _F = 50 A					4.01	V
I _{FAV}	average forward current	rectangular	d = 0.5	T _C = 90 °C			25	A
V _{F0}	threshold voltage	} for power loss calculation only			T _{VJ} = 150 °C		1.95	V
r _F	slope resistance						40	mΩ
R _{thJC}	thermal resistance junction to case						0.60	K/W
T _{VJ}	virtual junction temperature				-40		150	°C
P _{tot}	total power dissipation			T _C = 25 °C			210	W
I _{FSM}	max. forward surge current	t = 10 ms	(50 Hz), sine	T _{VJ} = 45 °C			250	A
I _{RM}	max. reverse recovery current			T _{VJ} = 25 °C		5.5		A
		I _F = 30 A; V _R = 600 V		T _{VJ} = 100 °C		12.5		A
t _{rr}	reverse recovery time	-di _F /dt = 600 A/μs		T _{VJ} = 25 °C		15		ns
				T _{VJ} = 100 °C		70		ns
C _J	junction capacitance	V _R = 400 V; f = 1 MHz		T _{VJ} = 25 °C		18		pF

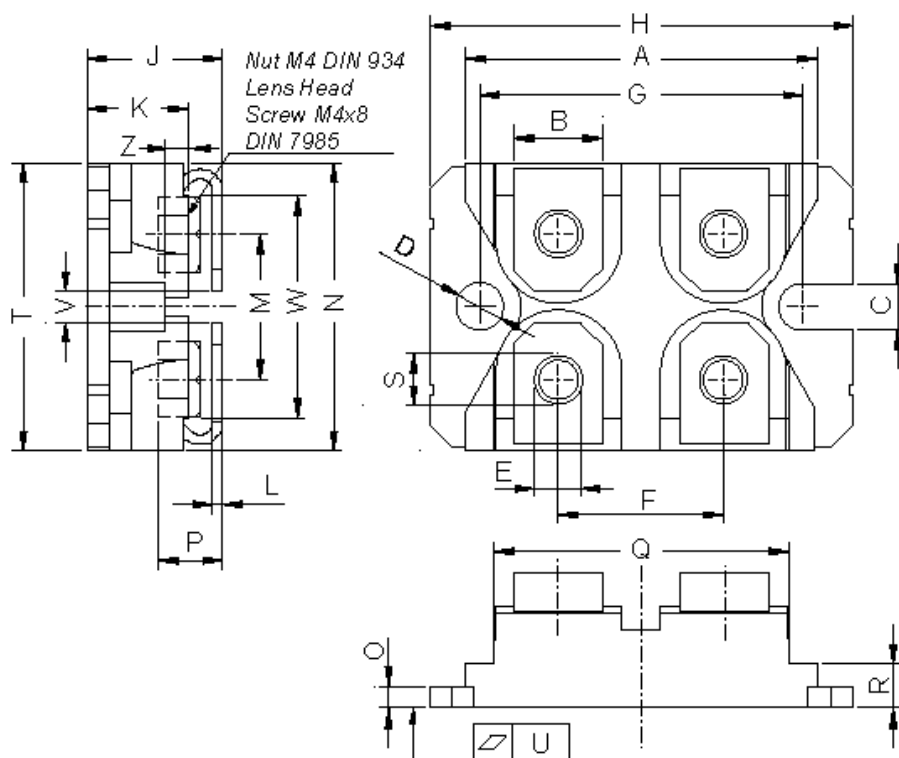
Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			100	A
R_{thCH}	thermal resistance case to heatsink			0.10		K/W
T_{stg}	storage temperature		-40		150	°C
Weight				30		g
M_D	mounting torque		1.1		1.5	Nm
M_T	terminal torque		1.1		1.5	Nm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V
$d_{Spp/App}$	creepage striking distance on surface through air	terminal to terminal	10.5	3.2		mm
$d_{Spb/Apb}$	creepage striking distance on surface through air	terminal to backside	8.6	6.8		mm

Product Marking



Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DSEP2x25-12C	DSEP2x25-12C	Tube	10	482021

Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106

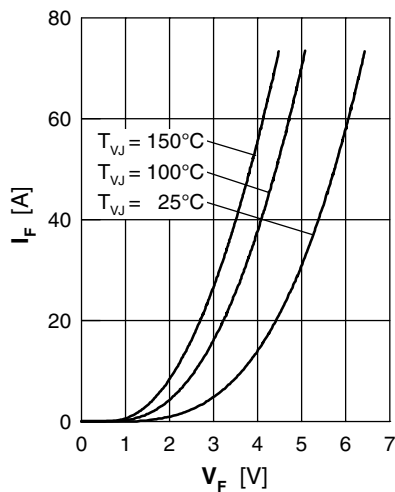


Fig. 1 Forward current I_F vs. V_F

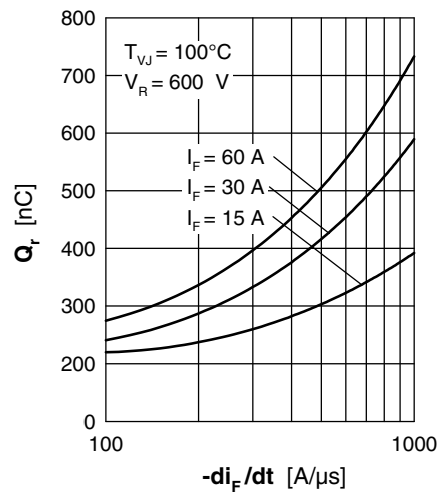


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

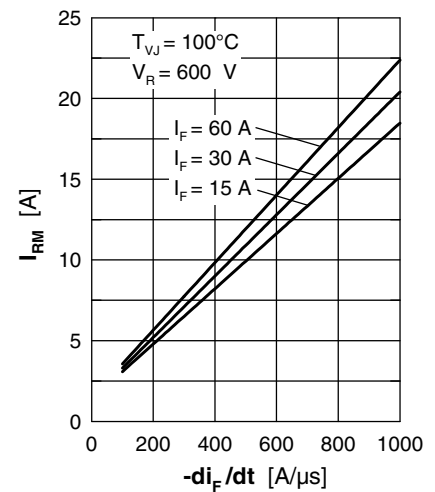


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

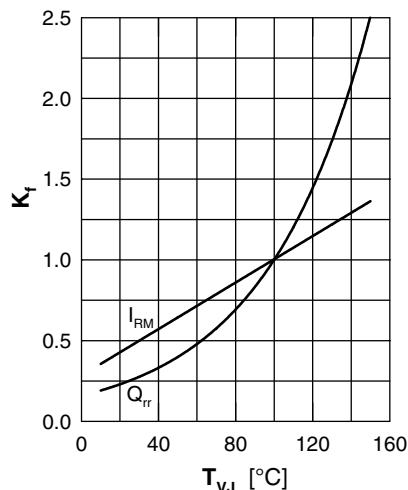


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

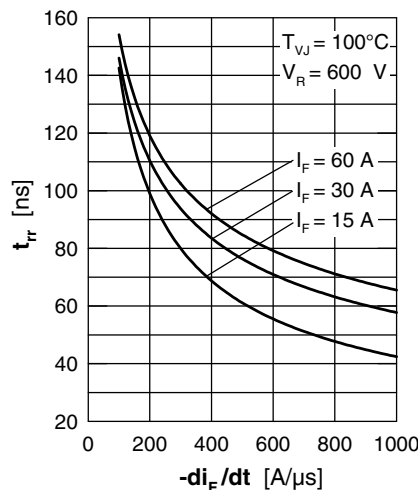


Fig. 5 Recovery time t_{rr} versus $-di_F/dt$

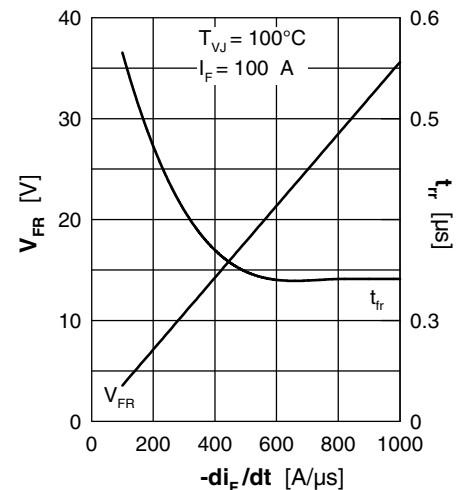


Fig. 6 Peak forward voltage V_{FR} and t_{fr} versus di_F/dt

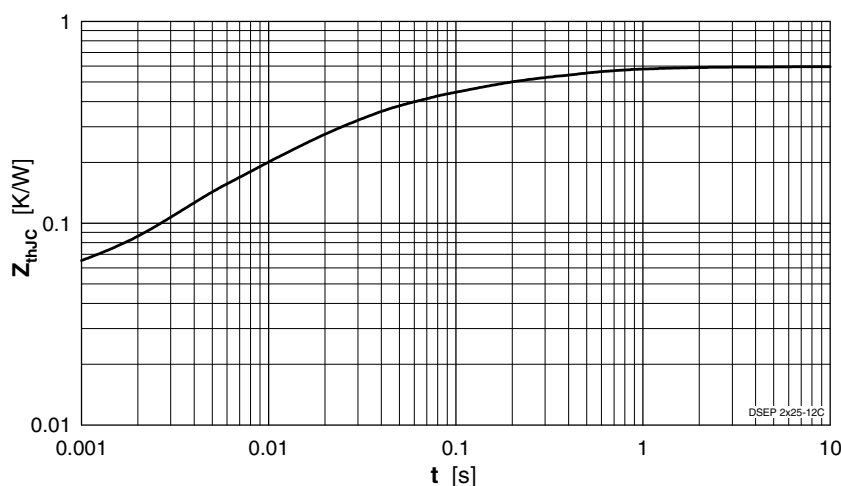


Fig. 7 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.037	0.00024
2	0.07	0.0036
3	0.246	0.0235
4	0.176	0.142
5	0.07	0.7